

## ■ GaAs FET MODULE FOR HANDY PHONE

Type No.	Application	Max. ratings					P <sub>o</sub> (min)							η <sub>T</sub> (%)	2nd Harm (min) (dB)	P <sub>in</sub> (max) (-)
		V <sub>o</sub> (V)	V <sub>g</sub> (V)	I <sub>b</sub> (A)	T <sub>C(OP)</sub> (°C)		f (MHz)		V <sub>b</sub> (V)	V <sub>g</sub> (V)	P <sub>in</sub> (dBm)	(dBm)				
FA01314	1710-1785MHz, 32.5dBm Power AMP. PCN	9	-5.5	1.0	-30	+90	1710	1785	5.8	-4	0	33.0	40	30	3	
FA01317	1429-1453MHz, 31.0dBm Power AMP. PDC 1500	9	-5.5	1.0	-30	+90	1429	1453	5.8	-4	0	31.0	35	30	3	
FA01319A	★ 1850-1910MHz, 33.0dBm Power AMP. PCS	9	-5.5	1.0	-30	+90	1850	1910	5.8	-4	0	33.0	35	30	3	
FA01215	★★ 880-915MHz, 35.0dBm Power AMP. GSM π	5.5	-4	2.5	-20	+85	880	915	3.0	-2.0	13	35.0	50	30	3	
FA01216	★ 925-958MHz, 31.0dBm Power AMP. PDC 800	4	-4	1.5	-20	+85	940	958	3.4	-2.4	7	31.0	45	30	3	
FA01219	★★ 925-958MHz, 30.5dBm Power AMP. PDC 800	4	-4	1.0	-20	+85	925	958	3.5	-2.5	7	30.5	45	20	3	
FA01220	★★ 1429-1453MHz, 30.5dBm Power AMP. PDC 1500	4	-4	1.0	-20	+85	1429	1453	3.5	-2.5	10	30.5	45	20	3	

## ■ GaAs MMIC FOR HANDY PHONE

Type No.	Application	Max. ratings				Electrical characteristics					
		V <sub>d1</sub> , V <sub>d2</sub> (V)	V <sub>g</sub> (V)	P <sub>in</sub> (dBm)	T <sub>C(OP)</sub> (°C)	Conditions		P <sub>in</sub> (dBm)	P <sub>o</sub> (Typ.) (dBm)	I <sub>t</sub> (Typ.) (mA)	
MGF7108A	Power AMP. (NTACS)	5	-3.5	12	-30 to +90	898 to 925		3.4	7	30.5	490 <sup>*1</sup>
MGF7109A	Power AMP. (NTT)	5	-3.5	12	-30 to +90	925 to 940		3.4	7	30.5	490 <sup>*1</sup>
MGF7110C	Power AMP. (NTACS)	9	-5	12	-30 to +90	898 to 925		4.7	7	30.5	400 <sup>*2</sup>
MGF7113C	Power AMP. (AMPS)	9	-5	12	-30 to +90	824 to 849		4.7	7	30.5	400 <sup>*2</sup>
MGF7114C	Power AMP. (ETACS)	9	-5	12	-30 to +90	872 to 905		4.7	7	30.5	400 <sup>*2</sup>
MGF7113P	★★ Power AMP. (AMPS)	9	-5	12	-30 to +85	824 to 849		4.7	7	31.0	380 <sup>*3</sup>
MGF7150C	★ Power AMP. (PCN)	9	-5	13	-30 to +85	1710 to 1785		4.7	10	33.5	940 <sup>*4</sup>
MGF7166C	★★ Power AMP. (PCN)	6.5	-4	13	-30 to +85	1710 to 1785		3.5	10	33.5	1400 <sup>*4</sup>
MGF7167C	★★ Power AMP. (PCS)	6.5	-4	13	-30 to +85	1850 to 1910		3.5	10	33.5	1400 <sup>*4</sup>
MGF7168C	★★ Power AMP. (PCS)	5	-4	15	-30 to +85	1850 to 1910		3.5	10	33.0	1250 <sup>*4</sup>

\*1. P<sub>apc</sub> = 29.3dBm \*2. P<sub>apc</sub> = 29.8dBm \*3. P<sub>apc</sub> = 30.0dBm \*4. P<sub>apc</sub> = 33.0dBm

Type No.	Application	Max. ratings				Electrical characteristics					
		V <sub>d1</sub> , V <sub>d2</sub> (V)	V <sub>g</sub> (V)	P <sub>in</sub> (dBm)	T <sub>C(OP)</sub> (°C)	Conditions		P <sub>in</sub> (dBm)	I <sub>t</sub> (Typ.) (mA)		
MGF7160C	★★ Power AMP. (PDC800)	5	-4	13	-30 to +80	925 to 956		3.5	-48	7 <sup>*5</sup>	660 <sup>*5</sup>
MGF7165C	★★ Power AMP. (PDC1500)	5	-4	13	-30 to +80	1429 to 1453		3.5	-48	8 <sup>*5</sup>	660 <sup>*5</sup>

\*5. P<sub>apc</sub> = 30.5dBm

## ■ 1.9GHz BAND GaAs MMIC

Type No.	Application	Max. ratings				Electrical characteristics					
		V <sub>d</sub> (V)	V <sub>g</sub> (V)	P <sub>in</sub> (dBm)	T <sub>C(OP)</sub> (°C)	Conditions		P <sub>o</sub> (dBm)	G <sub>p</sub> (dB)	I <sub>d(OP)</sub> (Typ.) (mA)	
MGF7121	Power AMP. (PHS)	6.0	-5.5	-5	-20 to +75	1890 to 1920		4.6	22	38	-
MGF7122	Power AMP. (PHS)	6.0	-5.5	-5	-20 to +75	1890 to 1920		3.4	21	34	-
MGF7124A	★ Power AMP. (PHS)	6.0	-5.5	10	-20 to +75	1890 to 1920		5.0	26	21	300
MGF7132P	Power AMP. (PHS)	5.0	-5.5	0	-20 to +75	1890 to 1920		3.4	21	28	175
MGF7132BP	Power AMP. (PHS)	5.0	-5.5	0	-20 to +75	1890 to 1920		3.1	21	28	175

Type No.	Application	Max. ratings		RF												Logic					
		V <sub>d</sub> (V)	P <sub>in</sub> (dBm)	f (MHz)	V <sub>d</sub> (V)	TX			RX			RF-switch			f (MHz)	V <sub>d</sub> (V)					
						P <sub>o</sub> (dBm)	G <sub>p</sub> (dB)	I <sub>d(OP)</sub> (mA)	GI (dB)	NF (dB)	I <sub>d(OP)</sub> (mA)	I.Loss (dB)	Iso (dB)	I.Loss (dB)			Iso (dB)	Loss (dB)			
MGF7134P	★ TX/RX front-end (PHS)	4.0	350	0	1890 to 1920	3.0	21.5	26	180	12	2.0	5.5	1.3	30	1.2	20	18.5	240	3.0	-8	5.0
MGF7135P	★★ TX/RX front-end (PHS)	4.0	350	0	1890 to 1920	3.0	21.0	26	140	13	2.0	4.0	0.7	20	0.7	20	-	-	-	-	-